**Product data sheet** 

## 1. General description

Dual ultrafast power diode in a SOT78 (TO-220AB) plastic package.

### 2. Features and benefits

- Soft recovery characteristic minimizes power consuming oscillations
- Very low on-state losses
- Fast switching
- High thermal cycling performance
- Low thermal resistance
- Low forward voltage drop

# 3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

## 4. Quick reference data

Table 1. Quick reference data

| Symbol             | Parameter                       | Conditions   | Values |     |     |      | Unit |
|--------------------|---------------------------------|--|--------|-----|-----|------|------|
| Absolute           | maximum rating                  |  |        |     |     |      |      |
| $V_{RRM}$          | repetitive peak reverse voltage |  |        | 4   | 00  |      | V    |
| I <sub>O(AV)</sub> | average output current          | SQW; $\delta$ = 0.5; $T_{mb} \le$ 115 °C; both diodes conducting; Fig. 1; Fig. 2                                       | 20     |     |     |      | А    |
| I <sub>FRM</sub>   | repetitive peak forward current | $δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 115 °C$ ; per diode   | 20     |     |     | А    |      |
| I <sub>FSM</sub>   | non-repetitive peak             | SIN; $t_p = 10 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$ ; per diode   |        | 1   | 20  | 20   |      |
|                    | forward current                 | SIN; $t_p = 8.3 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$ ; per diode  | 132    |     |     |      | Α    |
| Symbol             | Parameter                       | Conditions   |        | Min | Тур | Max  | Unit |
| Static ch          | aracteristics                   |  |        |     |     |      |      |
| V <sub>F</sub>     | forward voltage                 | $I_F = 10 \text{ A}; T_j = 150 \text{ °C}; Fig. 4$ - 0.87 1.   |        |     |     | 1.05 | V    |
| Dynamic            | characteristics                 |  |        |     |     |      |      |
| t <sub>rr</sub>    | reverse recovery time           | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 6; Fig. 7$ |        | -   | 50  | 60   | ns   |

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**BYV34-400** 

**Dual ultrafast power diode** 

# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | A1     | anode 1     | mb                 |                |
| 2   | K      | cathode     |                    | A              |
| 3   | A2     | anode 2     |                    | A1 A2 K sym125 |

# 6. Ordering information

#### **Table 3. Ordering information**

| Type number | Package  |   |         |
|-------------|----------|---|---------|
|             | Name     | Description   | Version |
| BYV34-400   | TO-220AB | plastic single-ended package; heatsink mounted;<br>1 mounting hole; 3-lead TO-220AB | SOT78   |

# 7. Marking

### **Table 4. Marking codes**

| Type number | Marking codes |
|-------------|---------------|
| BYV34-400   | BYV34-400     |

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# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                       | Conditions   | Values     | Unit |
|--------------------|---------------------------------|--|------------|------|
| $V_{RRM}$          | repetitive peak reverse voltage |  | 400        | V    |
| $V_{RWM}$          | crest working reverse voltage   |  | 400        | V    |
| $V_R$              | reverse voltage                 | T <sub>mb</sub> ≤ 138 °C; DC   | 400        | V    |
| I <sub>O(AV)</sub> | average output current          | SQW; $\delta$ = 0.5; $T_{mb} \le 115$ °C; both diodes conducting; Fig. 1; Fig. 2 | 20         | А    |
| I <sub>FRM</sub>   | repetitive peak forward current | $δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 115 °C$ ; per diode                   | 20         | Α    |
| I <sub>FSM</sub>   | non-repetitive peak             | SIN; $t_p = 10$ ms; $T_{j(init)} = 25$ °C; per diode                             | 120        | А    |
|                    | forward current                 | SIN; $t_p = 8.3 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$ ; per diode          | 132        | А    |
| T <sub>stg</sub>   | storage temperature             |  | -40 to 150 | °C   |
| Tj                 | junction temperature            |  | 150        | °C   |

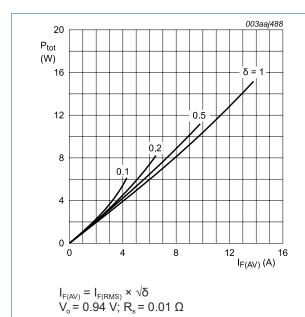


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

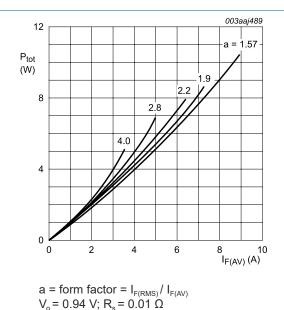


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

**Dual ultrafast power diode** 

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter   | Conditions                                     | Min | Тур | Max | Unit |
|-----------------------|---|--|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance from junction to               | with heatsink compound; both diodes conducting | -   | -   | 1.6 | K/W  |
|                       | mounting base                                     | with heatsink compound; per diode; Fig. 3      | -   | -   | 2.4 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient |  | -   | 60  | -   | K/W  |

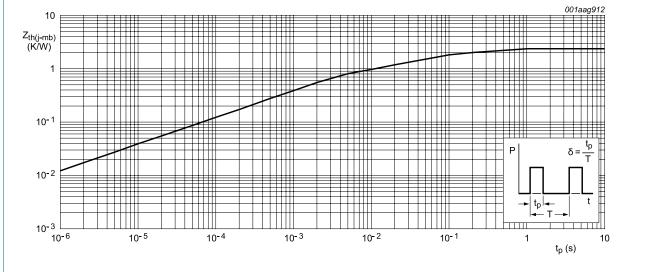


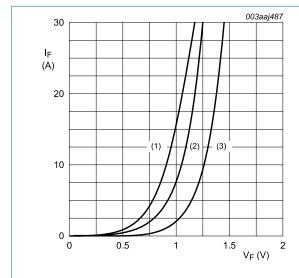
Fig. 3. Transient thermal impedance from junction to mounting base per diode as a function of pulse width

**Dual ultrafast power diode** 

## 10. Characteristics

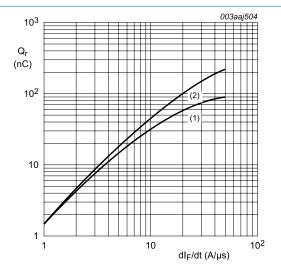
**Table 7. Characteristics** 

| Symbol           | Parameter                     | Conditions  | Min | Тур  | Max  | Unit |
|------------------|-------------------------------|---|-----|------|------|------|
| Static cha       | racteristics                  |   |     |      |      |      |
| V <sub>F</sub>   | forward voltage               | I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>  | -   | 1.1  | 1.35 | V    |
|                  |                               | I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>   | -   | 0.87 | 1.05 | V    |
| I <sub>R</sub>   | reverse current               | V <sub>R</sub> = 400 V; T <sub>j</sub> = 25 °C  | -   | 10   | 50   | μA   |
|                  |                               | V <sub>R</sub> = 400 V; T <sub>j</sub> = 100 °C   | -   | 0.2  | 0.6  | mA   |
| Dynamic          | characteristics               |   |     | '    |      |      |
| Q <sub>r</sub>   | recovered charge              | $I_F = 2 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 20 \text{ A/}\mu\text{s}$ ;<br>Fig. 5; Fig. 6                       | -   | 50   | 50   | nC   |
| t <sub>rr</sub>  | reverse recovery time         | $I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 6; Fig. 7 | -   | 50   | 60   | ns   |
| I <sub>RM</sub>  | peak reverse recovery current | $I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$<br>$T_j = 100 \text{ °C}; Fig. 6; Fig. 8$     | -   | 4    | 5    | А    |
| V <sub>FRM</sub> | forward recovery voltage      | $I_F = 10 \text{ A}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 9                               | -   | 2.5  | -    | V    |



(1)  $T_j$  = 150 °C; typical values (2)  $T_j$  = 150 °C; maximum values (3)  $T_j$  = 25 °C; maximum values  $V_o$  = 0.94 V;  $R_s$  = 0.01  $\Omega$ 

Fig. 4. Forward current as a function of forward voltage; per diode



(1)  $I_F = 2 \text{ A}$ ;  $T_j = 25 \text{ °C}$ (2)  $I_F = 20 \text{ A}$ ;  $T_j = 25 \text{ °C}$ 

Fig. 5. Recovered charge as a function of rate of change of forward current; per diode; maximum values

#### **Dual ultrafast power diode**

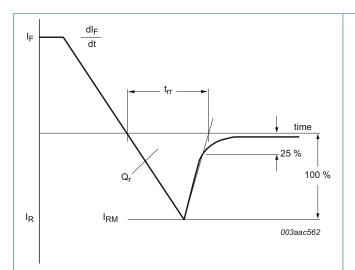
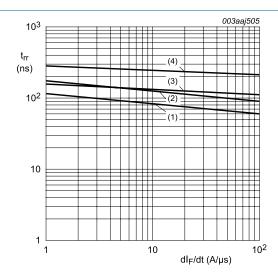


Fig. 6. Reverse recovery definitions; ramp recovery



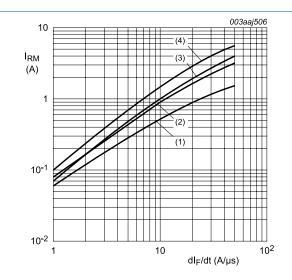
(1) 
$$I_F$$
 = 1 A;  $T_j$  = 25 °C

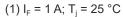
(2) 
$$I_F = 1 A$$
;  $T_j = 100 \,^{\circ}\text{C}$ 

(3) 
$$I_F = 20 \text{ A}$$
;  $T_i = 25 \text{ °C}$ 

(4) 
$$I_F = 20 \text{ A}$$
;  $T_j = 100 \text{ °C}$ 

Fig. 7. Reverse recovery time as a function of rate of change of forward current; per diode; maximum values





(2) 
$$I_F = 1 A$$
;  $T_i = 100 \,^{\circ}C$ 

(3) 
$$I_F = 20 \text{ A}$$
;  $T_i = 25 \text{ °C}$ 

(4) 
$$I_F = 20 \text{ A}$$
;  $T_i = 100 \,^{\circ}\text{C}$ 

Fig. 8. Peak reverse recovery current as a function of rate of change of forward current; per diode; maximum values

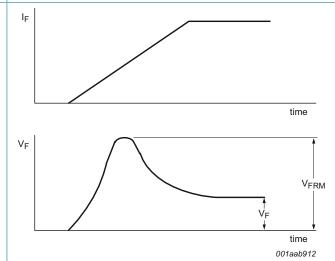
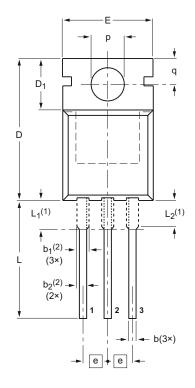


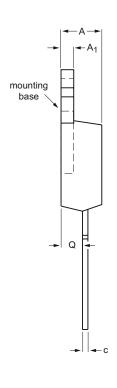
Fig. 9. Forward recovery definitions

# 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

**SOT78** 





0 5 10 mm

#### **DIMENSIONS** (mm are the original dimensions)

| UNIT | Α          | A <sub>1</sub> | b          | b <sub>1</sub> <sup>(2)</sup> | b <sub>2</sub> <sup>(2)</sup> | С          | D            | D <sub>1</sub> | E           | е    | L            | L <sub>1</sub> <sup>(1)</sup> | L <sub>2</sub> <sup>(1)</sup><br>max. | р          | q          | Q          |
|------|------------|----------------|------------|-------------------------------|-------------------------------|------------|--------------|----------------|-------------|------|--------------|-------------------------------|---------------------------------------|------------|------------|------------|
| mm   | 4.7<br>4.1 | 1.40<br>1.25   | 0.9<br>0.6 | 1.6<br>1.0                    | 1.3<br>1.0                    | 0.7<br>0.4 | 16.0<br>15.2 | 6.6<br>5.9     | 10.3<br>9.7 | 2.54 | 15.0<br>12.8 | 3.30<br>2.79                  | 3.0                                   | 3.8<br>3.5 | 3.0<br>2.7 | 2.6<br>2.2 |

#### Notes

- Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE |   |     | REFER           | EUROPEAN | ISSUE DATE |            |                                 |
|---------|---|-----|-----------------|----------|------------|------------|---------------------------------|
| VERSION | 1 | IEC | JEDEC           | JEITA    |            | PROJECTION | ISSUE DATE                      |
| SOT78   |   |     | 3-lead TO-220AB | SC-46    |            |            | <del>08-04-23</del><br>08-06-13 |

#### **Dual ultrafast power diode**

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#### Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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**Dual ultrafast power diode** 

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### **Dual ultrafast power diode**

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For more information, please visit: http://www.ween-semi.com For sales office addresses, please send an email to: salesaddresses@ween-semi.com Date of release: 8 June 2018

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